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REVOCATION AND NEW POWER OF ATTORNEY AND CHANGE OF CORRESPONDENCE ADDRESS

I, ***Dr. Graham Fisher, Director of Intellectual Property*** of ***MEMC Electronic Materials, Inc.***, the Assignee of the entire right, title, and interest in the ***U.S. Patent Application(s) and/or Patent(s) identified on the attached Schedule A***, hereby revoke all previous powers of attorney or authorizations of agent given and do hereby appoint the attorneys or agents associated with the following Customer Number, with full power of substitution and revocation, to prosecute and transact all business in the Patent and Trademark Office connected therewith for the ***U.S. Patent Application(s) and/or Patent(s) listed in the attached Schedule A:***

Customer Number: 76681

Please direct all correspondence in connection with said ***U.S. Patent Application(s) and/or Patent(s)*** to:

Customer Number: 76681

Respectfully submitted,

Date: 5/13/2008

Dr. Graham Fisher
Director of Intellectual Property
MEMC Electronic Materials, Inc.

PATENT

THE UNITED STATES PATENT AND TRADEMARK OFFICE

STATEMENT UNDER 37 CFR 3.73(b)

MEMC Electronic Materials, Inc., a Delaware Corporation, pursuant to 37 CFR 3.73(b), hereby states that it is the Assignee of the entire right, title, and interest in ***U.S. Patent Application(s) and/or Patent(s) on the attached Schedule A.***

The entire rights, title, and interest in the aforementioned Patent Application(s) and/or Patent(s) were conveyed to ***MEMC Electronic Materials, Inc.*** via Assignment(s) recorded with the United States Patent and Trademark Office at the ***Reel/Frame Numbers on the attached Schedule A.***

The undersigned, ***Dr. Graham Fisher, Director of Intellectual Property,*** has full authorization to act on behalf of Assignee ***MEMC Electronic Materials, Inc.***

Respectfully submitted,

Date: 5/13/2008

Dr. Graham Fisher
Director of Intellectual Property
MEMC Electronic Materials, Inc.

APPENDIX A
Owned by MEMC Electronic Materials, Inc.

ATTORNEY REFERENCE	CONF. NO	PUBLICATION NO. & DATE	SERIAL NO. FILING DATE	PATENT NO. ISSUE DATE	CURRENT OWNER/ ASSIGNEE	REEL AND FRAME NO.	TITLE
MEMC2690	1463		09/521,288 3/8/2000	6,319,313 11/20/2001	MEMC Electronic Materials, Inc.	010818/0660 and 012139/0400	BARIUM DOPING OF MOLTEN SILICON FOR USE IN CRYSTAL GROWING PROCESS
MEMC2690.1	4490	US-2001-0032580-A1 10/25/2001	09/859,826 5/17/2001	6,461,427 10/8/2002	MEMC Electronic Materials, Inc.	012139/0410	BARIUM DOPING OF MOLTEN SILICON FOR USE IN CRYSTAL GROWING PROCESS
MEMC2691	6878		09/506,105 2/17/2000	6,376,335 4/23/2002	MEMC Electronic Materials, Inc.	010818/0439	SEMICONDUCTOR WAFER MANUFACTURING PROCESS
MEMC2704	6472		09/711,198 11/9/2000	6,454,851 9/24/2002	MEMC Electronic Materials, Inc.	011265/0157	METHOD AND APPARATUS FOR PREPARING MOLTEN SILICON MELT FROM POLYCRYSTALLINE SILICON CHARGE
MEMC2763	2067	US-2002-0084566-A1 7/4/2002	09/751,897 12/28/2000	6,497,403 12/24/2002	MEMC Electronic Materials, Inc.	011605/0469	SEMICONDUCTOR WAFER HOLDER
MEMC2764.1	2338	US-2003-0054641-A1 3/20/2003	10/120,714 4/11/2002	6,897,084 5/24/2005	MEMC Electronic Materials, Inc.	013007/0300	CONTROL OF OXYGEN PRECIPITATE FORMATION IN HIGH RESISTIVITY CZ SILICON
MEMC2764.7	7881	US-2005-0158969-A1 7/21/2005	11/082,267 3/17/2005	7,135,351 11/14/2006	MEMC Electronic Materials, Inc.	Division of 10/120,714 recorded at 013007/0300	METHOD FOR CONTROLLING OF THERMAL DONOR FORMATION IN HIGH RESISTIVITY CZ SILICON
MEMC2784	7794		09/681,160 2/2/2001	6,398,631 6/4/2002	MEMC Electronic Materials, Inc.	011477/0604	METHOD AND APPARATUS TO PLACE WAFERS INTO AND OUT OF MACHINE
MEMC2788.1	7155	US-2002-0052064-A1 5/2/2002	09/928,559 8/13/2001	6,709,981 3/23/2004	MEMC Electronic Materials, Inc.	012431/0085	METHOD AND APPARATUS FOR PROCESSING A SEMICONDUCTOR WAFER USING NOVEL FINAL POLISHING METHOD
MEMC2803	4008	US-2003-0077128-A1 4/24/2003	10/035,456 10/23/2001	6,609,870 8/26/2003	MEMC Electronic Materials, Inc.	012817/0489	GRANULAR SEMICONDUCTOR MATERIAL TRANSPORT SYSTEM AND PROCESS
MEMC2806.1	7221	US-2002-0121238-A1 9/5/2002	10/039,196 1/2/2002	6,986,925 1/17/2006	MEMC Electronic Materials, Inc.	012720/0452	SINGLE CRYSTAL SILICON HAVING IMPROVED GATE OXIDE INTEGRITY
28744-166 (MEMC2806.9)	2035	US2005-0160967 A1 7/28/2005	11/089,102 3/24/2005		MEMC Electronic Materials, Inc.	Division of 10/039,196 recorded at 012720/0452	PROCESS FOR PREPARING SINGLE CRYSTAL SILICON HAVING IMPROVED GATE OXIDE INTEGRITY
MEMC2809.6	4970	US-2003-0209186-A1 11/13/2003	10/204,654 11/4/2002	6,869,477 3/22/2005	MEMC Electronic Materials, Inc.	013478/0217	CONTROLLED NECK GROWTH PROCESS FOR SINGLE CRYSTAL SILICON
MEMC2810	2027		09/684,266 10/6/2000	6,482,263 11/19/2002	MEMC Electronic Materials, Inc.	011642/0278	HEAT SHIELD ASSEMBLY FOR CRYSTAL PULLING APPARATUS
MEMC2880.1	8911	US-2002-0174828-A1 11/28/2002	10/113,378 3/29/2002	6,743,495 6/1/2004	MEMC Electronic Materials, Inc.	013964/0378	THERMAL ANNEALING PROCESS FOR PRODUCING SILICON WAFERS WITH IMPROVED SURFACE CHARACTERISTICS
MEMC2888	5221		09/704,893 11/2/2000	6,586,068 7/1/2003	MEMC Electronic Materials, Inc.	Continuation of 09/030,110 recorded at 009389/0565	IDEAL OXYGEN PRECIPITATING SILICON WAFERS HAVING AN ASYMMETRICAL VACANCY CONCENTRATION PROFILE AND A PROCESS FOR THE PREPARATION THEREOF